

Title (en)

LED SEMICONDUCTOR BODY AND USE OF AN LED SEMICONDUCTOR BODY

Title (de)

LED-HALBLEITERKÖRPER UND VERWENDUNG EINES LED-HALBLEITERKÖRPERS

Title (fr)

ÉLÉMENT SEMI-CONDUCTEUR DEL ET SON UTILISATION

Publication

EP 2067179 A1 20090610 (DE)

Application

EP 07817459 A 20070828

Priority

- DE 2007001536 W 20070828
- DE 102006046037 A 20060928

Abstract (en)

[origin: DE102006046037A1] The light emitting diode semiconductor body (1) has a radiation generating active layers (31,32) and a photonic crystal (6). The photonic crystal has a number of areas (6a) with a refractive index and another number of areas (6b) with another refractive index. The reflection layer contains materials like aluminum, zinc and silver, a transparent conductive oxide, silicon nitride. The semiconductor body, particularly one of the two active layers or both active layers, containing compound consist of aluminium, gallium, indium, phosphorus, arsenic and nitrogen.

IPC 8 full level

H01L 33/08 (2010.01); **H01L 33/20** (2010.01)

CPC (source: EP US)

H01L 33/08 (2013.01 - EP US); **H01L 33/20** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US); **H01L 2933/0083** (2013.01 - EP US)

C-Set (source: EP US)

H01L 2924/0002 + **H01L 2924/00**

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DE FR GB

Designated extension state (EPC)

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